



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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12/6/02

Application of: Raulf M. Polichar, et al.

Application No.: 09/736,157

Examiner: KIN CHAN CHEN

Filed: December 15, 2000

Group Art Unit: 1765

Atty. Docket No.: SAIC0010-US

For: PIN ALLOY-SEMICONDUCTOR, RADIATION DETECTORS WITH RECTIFYING JUNCTION CONTACTS, METHODS AND SYSTEMS FOR FORMING PIN ALLOY-SEMICONDUCTOR DEVICES WITH RECTIFYING JUNCTION CONTACTS, AND SYSTEMS AND METHODS FOR ANALYZING ALLOY-SEMICONDUCTOR PROPERTIES

**RESPONSE TO ELECTION/RESTRICTIONS REQUIREMENT**

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Office Action dated September 5, 2002, the undersigned representative respectfully requests entry of the following amendments and remarks into the file of the above-identified application.

**In the Claims:**

Please add claims 25-44 as follows:

25. A method for forming an N-type contact on an alloy-semiconductor material comprising a compound having at least a first component, the method comprising photo-electrochemical reduction of the first component to form the N-type contact.

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